

In the Specification:

Please delete replacement paragraph [0088] for page 31 of the specification that was submitted on December 12, 2003 and replace it with the new replacement paragraph, marked to show the changes made, set forth below.

Composition concentrations, for one example, are shown in Table 7 and it should be noted that the concentration of, *inter alia*, the Insoluble Complexing Agent of the present invention may be changed to alter the resultant slurry. The concentration of Insoluble Complexing Agent 1,6-dioxaspirol [4,4] nonane 2,7-dione used for etching tests was from about 0.01% to about 0.2 % by weight. As used for CMP, the concentration was from about 0.05% to about 0.1%.

In Table 9, on page 37 of the specification, in the line directly below the text "CMP Process (A)", in the line directly below the text "CMP Process (B)", and in the line directly below the text "CMP Process (C)", please add the text set forth below.

s/pp/ts/ss